February 19, 2008



## DS90LV001 800 Mbps LVDS Buffer

### **General Description**

The DS90LV001 LVDS-LVDS Buffer takes an LVDS input signal and provides an LVDS output signal. In many large systems, signals are distributed across backplanes, and one of the limiting factors for system speed is the "stub length" or the distance between the transmission line and the unterminated receivers on individual cards. Although it is generally recognized that this distance should be as short as possible to maximize system performance, real-world packaging concerns often make it difficult to make the stubs as short as the designer would like.

The DS90LV001, available in the LLP (Leadless Leadframe Package) package, will allow the receiver to be placed very close to the main transmission line, thus improving system performance.

A wide input dynamic range will allow the DS90LV001 to receive differential signals from LVPECL as well as LVDS sources. This will allow the device to also fill the role of an LVPECL-LVDS translator.

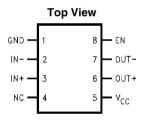
An output enable pin is provided, which allows the user to place the LVDS output in TRI-STATE.

The DS90LV001 is offered in two package options, an 8 pin LLP and SOIC.

#### **Features**

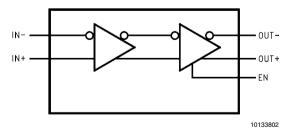
- Single +3.3 V Supply
- LVDS receiver inputs accept LVPECL signals
- TRI-STATE outputs
- Receiver input threshold < ±100 mV</p>
- Fast propagation delay of 1.4 ns (typ)
- Low jitter 800 Mbps fully differential data path
- 100 ps (typ) of pk-pk jitter with PRBS = 2<sup>23</sup>-1 data pattern at 800 Mbps
- Compatible with ANSI/TIA/EIA-644-A LVDS standard
- 8 pin SOIC and space saving (70%) LLP package
- Industrial Temperature Range

### **Connection Diagram**



Order Number DS90LV001TM, DS90LV001TLD See NS Package Number M08A, LDA08A

## **Block Diagram**



## **Absolute Maximum Ratings** (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

Supply Voltage (V<sub>CC</sub>) -0.3V to +4V LVCMOS/LVTTL Input Voltage

(EN)  $-0.3V \text{ to } (V_{CC} + 0.3V)$ 

LVDS Receiver Input Voltage (IN

+, IN-) -0.3V to +4V

LVDS Driver Output Voltage (OUT

+, OUT-)

LVDS Output Short Circuit Current

Junction Temperature

Storage Temperature Range

-0.3V to +4V

Continuous

+150°C

-65°C to +150°C

Lead Temperature Range

Soldering (4 sec.) +260°C

Maximum Package Power Dissipation at 25°C

M Package 726 mW

Derate M Package 5.8 mW/°C above +25°C

LDA Package 2.44 W

Derate LDA Package 19.49 mW/°C above +25°C

**ESD Ratings** 

(HBM, 1.5kΩ, 100pF) ≥2.5kV (EIAJ, 0Ω, 200pF) ≥250V

# Recommended Operating Conditions

	Min	Тур	Max	Units
Supply Voltage (V <sub>CC</sub> )	3.0	3.3	3.6	V
Receiver Input Voltage	0		$V_{CC}$	V
Operating Free Air	-40	+25	+85	°C

#### **Electrical Characteristics**

Over recommended operating supply and temperature ranges unless otherwise specified. (Notes 2, 3)

Symbol	Parameter	Conditions		Min	Тур	Max	Units
LVCMOS	S/LVTTL DC SPECIFICATIONS (EN)						
V <sub>IH</sub>	High Level Input Voltage			2.0		V <sub>CC</sub>	V
V <sub>IL</sub>	Low Level Input Voltage			GND		0.8	V
I <sub>IH</sub>	High Level Input Current	$V_{IN} = 3.6V \text{ or } 2$	$0.0V, V_{CC} = 3.6V$		+7	+20	μΑ
I <sub>IL</sub>	Low Level Input Current	V <sub>IN</sub> = GND or 0	$0.8V, V_{CC} = 3.6V$		±1	±10	μΑ
V <sub>CL</sub>	Input Clamp Voltage	I <sub>CL</sub> = -18 mA			-0.6	-1.5	V
LVDS O	UTPUT DC SPECIFICATIONS (OUT)	•		•	•	•	
V <sub>OD</sub>	Differential Output Voltage	R <sub>L</sub> = 100Ω		250	325	450	mV
ΔV <sub>OD</sub>	Change in Magnitude of V <sub>OD</sub> for Complimentary Output States	Figure 1 and Figure 2				20	mV
V <sub>os</sub>	Offset Voltage	$R_L = 100\Omega$		1.080	1.19	1.375	V
ΔV <sub>OS</sub>	Change in Magnitude of V <sub>OS</sub> for Complimentary Output States	Figure 1				20	mV
I <sub>OZ</sub>	Output TRI-STATE Current	EN = 0V, V <sub>OUT</sub> = V <sub>CC</sub> or GND			±1	±10	μA
I <sub>OFF</sub>	Power-Off Leakage Current	V <sub>CC</sub> = 0V, V <sub>OUT</sub> = 3.6V or GND			±1	±10	μA
I <sub>os</sub>	Output Short Circuit Current (Note 4)	$EN = V_{CC}, V_{OUT+}$ and $V_{OUT-} = 0V$			-16	-24	mA
I <sub>OSD</sub>	Differential Output Short Circuit Current (Note 4)	$EN = V_{CC}, V_{OD} = 0V$			-7	-12	mA
LVDS RI	ECEIVER DC SPECIFICATIONS (IN)	•			•	•	
V <sub>TH</sub>	Differential Input High Threshold	V <sub>CM</sub> = +0.05V, +1.2V or +3.25V			0	+100	mV
$\overline{V_{TL}}$	Differential Input Low Threshold	7		-100	0		mV
V <sub>CMR</sub>	Common Mode Voltage Range	V <sub>ID</sub> = 100mV, V <sub>CC</sub> = 3.3V		0.05		3.25	V
I <sub>IN</sub>	Input Current	$V_{IN} = +3.0V$	V <sub>CC</sub> = 3.6V or 0V		±1	±10	μΑ
		$V_{IN} = 0V$			±1	±10	μA
ΔΙ <sub>ΙΝ</sub>	Change in Magnitude of I <sub>IN</sub>	$V_{IN} = +3.0V$	V <sub>CC</sub> = 3.6V or 0V		1	6	μA
		$V_{IN} = 0V$			1	6	μΑ
SUPPLY	CURRENT	,	1				
I <sub>CCD</sub>	Total Supply Current	$EN = V_{CC}, R_L = 100\Omega, C_L = 5 pF$			47	70	mA
I <sub>CCZ</sub>	TRI-STATE Supply Current	EN = 0V			22	35	mA

#### **AC Electrical Characteristics**

Over recommended operating supply and temperature ranges unless otherwise specified. (Note 3)

Symbol	Parameter	Conditions	Min	Тур	Max	Units
t <sub>PHLD</sub>	Differential Propagation Delay High to Low	$R_L = 100\Omega, C_L = 5pF$	1.0	1.4	2.0	ns
t <sub>PLHD</sub>	Differential Propagation Delay Low to High	Figure 3 and Figure 4	1.0	1.4	2.0	ns
t <sub>SKD1</sub>	Pulse Skew It <sub>PLHD</sub> – t <sub>PHLD</sub> I (Notes 5, 6)			20	200	ps
t <sub>SKD3</sub>	Part to Part Skew (Notes 5, 7)			0	60	ps
t <sub>SKD4</sub>	Part to Part Skew (Notes 5, 8)				400	ps
t <sub>LHT</sub>	Rise Time (Note 5)	$R_{L} = 100\Omega, C_{L} = 5pF$	200	320	450	ps
t <sub>HLT</sub>	Fall Time (Note 5)	Figure 3 and Figure 5	200	310	450	ps
t <sub>PHZ</sub>	Disable Time (Active High to Z)	$R_{L} = 100\Omega, C_{L} = 5pF$		3	25	ns
t <sub>PLZ</sub>	Disable Time (Active Low to Z)	Figure 6 and Figure 7		3	25	ns
t <sub>PZH</sub>	Enable Time (Z to Active High)			25	45	ns
t <sub>PZL</sub>	Enable Time (Z to Active Low)			25	45	ns
t <sub>DJ</sub>	LVDS Data Jitter, Deterministic (Peak-to-Peak) (Note 9)	$V_{ID} = 300 \text{mV}$ ; PRBS = $2^{23} - 1 \text{ data}$ ; $V_{CM} = 1.2 \text{V at } 800 \text{Mbps (NRZ)}$		100	135	ps
t <sub>RJ</sub>	LVDS Clock Jitter, Random (Note 9)	$V_{ID} = 300$ mV; $V_{CM} = 1.2$ V at 400MHz clock		2.2	3.5	ps

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the device should be operated at these limits. The table of "Electrical Characteristics" specifies conditions of device operation.

Note 2: Current into device pins is defined as positive. Current out of device pins is defined as negative. All voltages are referenced to ground except  $V_{OD}$  and  $\Delta V_{OD}$ .

**Note 3:** All typical are given for  $V_{CC} = +3.3V$  and  $T_A = +25^{\circ}C$ , unless otherwise stated.

Note 4: Output short circuit current ( $I_{OS}$ ) is specified as magnitude only, minus sign indicates direction only.

Note 5: The parameters are guaranteed by design. The limits are based on statistical analysis of the device performance over the PVT (process, voltage and temperature) range.

Note 6: t<sub>SKD1</sub>, lt<sub>PLHD</sub> - t<sub>PHLD</sub>I, is the magnitude difference in differential propagation delay time between the positive going edge and the negative going edge of the same channel.

Note 7: t<sub>SKD3</sub>, Part to Part Skew, is defined as the difference between the minimum and maximum specified differential propagation delays. This specification applies to devices at the same V<sub>CC</sub> and within 5°C of each other within the operating temperature range.

Note 8: t<sub>SKD4</sub>, Part to Part Skew, is the differential channel-to- channel skew of any event between devices. This specification applies to devices over recommended operating temperature and voltage ranges, and across process distribution. t<sub>SKD4</sub> is defined as IMax – MinI differential propagation delay.

**Note 9:** The parameters are guaranteed by design. The limits are based on statistical analysis of the device performance over the PVT range with the following test equipment setup: HP8133A (pattern pulse generator), 5 feet of RG142B cable with DUT test board and HP83480A (digital scope mainframe) with HP83484A (50GHz scope module). The HP8133A with RG142B cable exhibit a t<sub>DJ</sub> = 21ps and t<sub>RJ</sub> = 1.8ps.

## **DC Test Circuits**

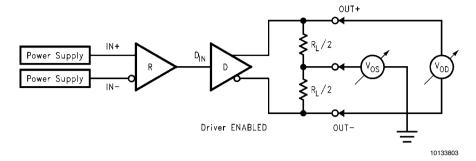


FIGURE 1. Differential Driver DC Test Circuit

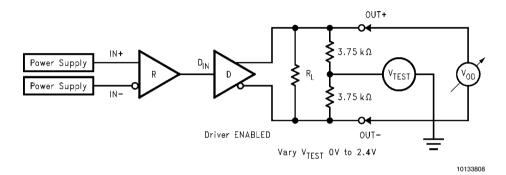


FIGURE 2. Differential Driver Full Load DC Test Circuit

## **AC Test Circuits and Timing Diagrams**

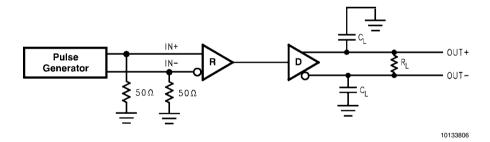


FIGURE 3. LVDS Output Load

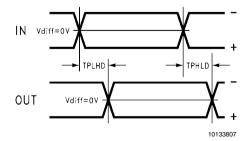


FIGURE 4. Propagation Delay Low-to-High and High-to-Low

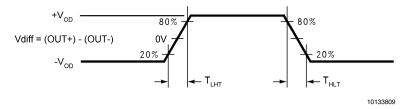


FIGURE 5. LVDS Output Transition Time

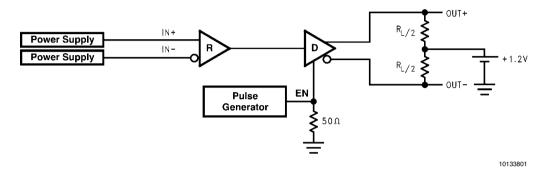


FIGURE 6. TRI-STATE Delay Test Circuit

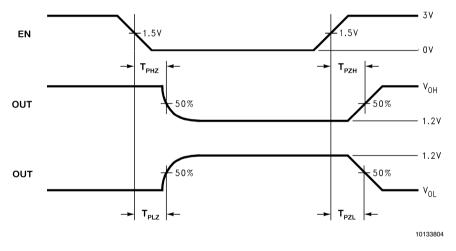


FIGURE 7. Output active to TRI-STATE and TRI-STATE to active output time

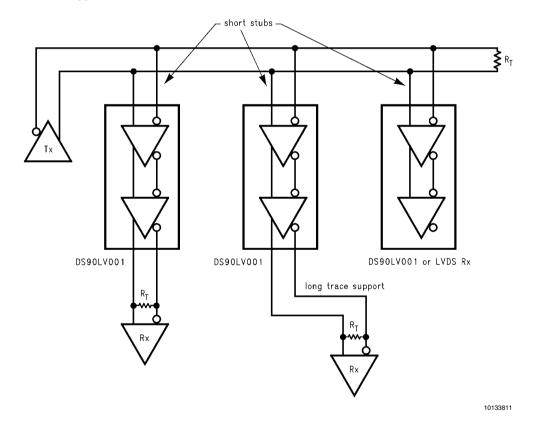
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## DS90LV001 Pin Descriptions (SOIC and LLP)

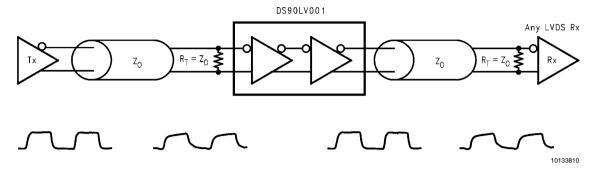
Pin Name	Pin #	Input/Output	Description	
GND	1	Р	Ground	
IN –	2	I	Inverting receiver LVDS input pin	
IN+	3	I	Non-inverting receiver LVDS input pin	
NC	4		No Connect	
V <sub>CC</sub>	5	Р	Power Supply, 3.3V ± 0.3V.	
OUT+	6	0	Non-inverting driver LVDS output pin	
OUT -	7	0	Inverting driver LVDS output pin	
EN	8	I	Enable pin. When EN is LOW, the driver is disabled and the LVDS outputs are in TRI-STATE. When EN is HIGH, the driver is enabled. LVCMOS/LVTTL levels.	
DAP	NA	NA	Die Attach Pad or DAP (LLP Package only). The DAP is NOT connected to the device GND nor any other pin. It is still recommended to connect the DAP to a GND plane of a PCB for enhenced heat dissipation.	

## **Typical Applications**

**Backplane Stub-Hider Application** 



#### **Cable Repeater Application**



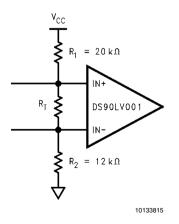
## **Application Information**

#### MODE OF OPERATION

The DS90LV001 can be used as a "stub-hider." In many systems, signals are distributed across backplanes, and one of the limiting factors for system speed is the "stub length" or the distance between the transmission line and the unterminated receivers on the individual cards. Although it is generally recognized that this distance should be as short as possible to maximize system performance, real-world packaging concerns and PCB designs often make it difficult to make the stubs as short as the designer would like. The DS90LV001, available in the LLP (Leadless Leadframe Package) package. can improve system performance by allowing the receiver to be placed very close to the main transmission line either on the backplane itself or very close to the connector on the card. Longer traces to the LVDS receiver may be placed after the DS90LV001. This very small LLP package is a 75% space savings over the SOIC package.

#### INPUT FAILSAFE

The receiver inputs of the DS90LV001 do not have internal failsafe biasing. For point-to-point and multidrop applications with a single source, failsafe biasing may not be required. When the driver is off, the link is in-active. If failsafe biasing is required, this can be accomplished with external high value resistors. Using the equations in the LVDS Owner's Manual Chapter 4, the IN+ should be pull to  $V_{\rm CC}$  (3.3V) with 20k $\Omega$  and the IN- should be pull to GND with 12k $\Omega$ . This provides a slight positive differential bias, and sets a known HIGH state on the link with a minimum amount of distortion.



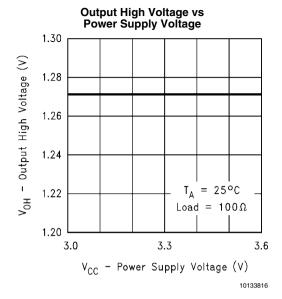
#### PCB LAYOUT AND POWER SYSTEM BYPASS

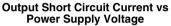
Circuit board layout and stack-up for the DS90LV001 should be designed to provide noise-free power to the device. Good layout practice also will separate high frequency or high level inputs and outputs to minimize unwanted stray noise pickup. feedback and interference. Power system performance may be greatly improved by using thin dielectrics (4 to 10 mils) for power/ground sandwiches. This increases the intrinsic capacitance of the PCB power system which improves power supply filtering, especially at high frequencies, and makes the value and placement of external bypass capacitors less critical. External bypass capacitors should include both RF ceramic and tantalum electrolytic types. RF capacitors may use values in the range 0.01 μF to 0.1 μF. Tantalum capacitors may be in the range 2.2 µF to 10 µF. Voltage rating for tantalum capacitors should be at least 5X the power supply voltage being used. It is recommended practice to use two vias at each power pin of the DS90LV001 as well as all RF bypass capacitor terminals. Dual vias reduce the interconnect inductance by up to half, thereby reducing interconnect inductance and extending the effective frequency range of the bypass components.

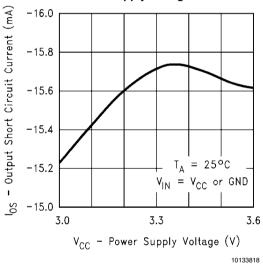
The outer layers of the PCB may be flooded with additional ground plane. These planes will improve shielding and isolation as well as increase the intrinsic capacitance of the power supply plane system. Naturally, to be effective, these planes must be tied to the ground supply plane at frequent intervals with vias. Frequent via placement also improves signal integrity on signal transmission lines by providing short paths for image currents which reduces signal distortion. The planes should be pulled back from all transmission lines and component mounting pads a distance equal to the width of the widest transmission line or the thickness of the dielectric separating the transmission line from the internal power or ground plane(s) whichever is greater. Doing so minimizes effects on transmission line impedances and reduces unwanted parasitic capacitances at component mounting pads.

There are more common practices which should be followed when designing PCBs for LVDS signaling. Please see application note AN-1108 for guidelines. In addition, application note AN-1187 has additional information specifically related to LLP recommendations.

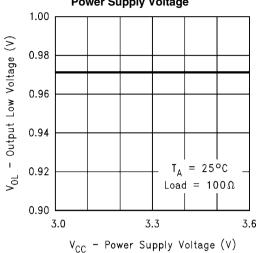
## **Typical Performance Curves**



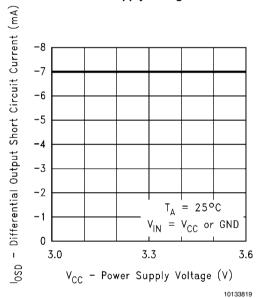


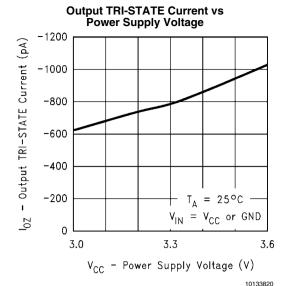


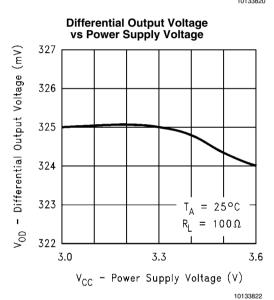
#### Output Low Voltage vs Power Supply Voltage

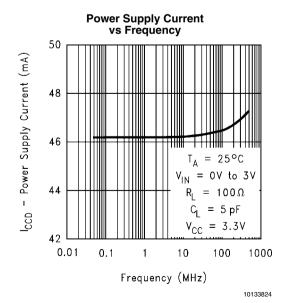


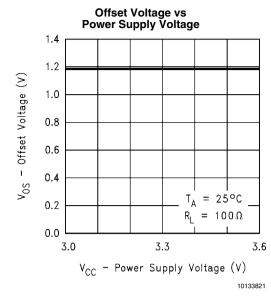
#### Differential Output Short Circuit Current vs Power Supply Voltage

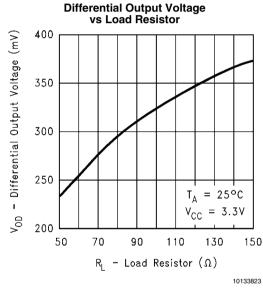


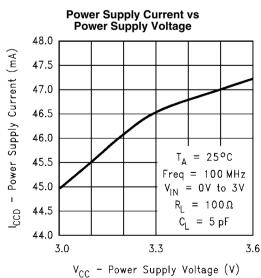






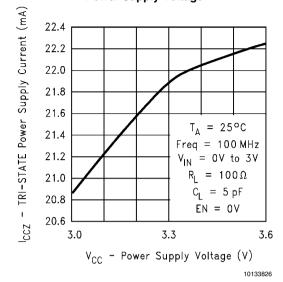




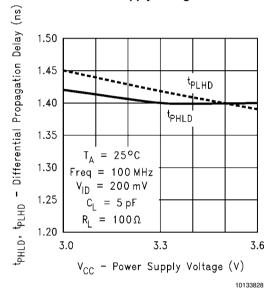


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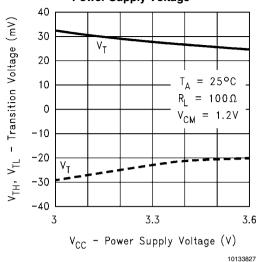
#### TRI-STATE Power Supply Current vs Power Supply Voltage



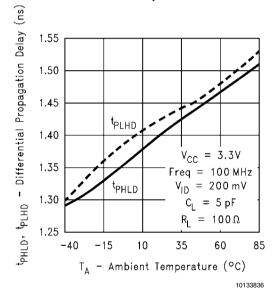
#### Differential Propagation Delay vs Power Supply Voltage



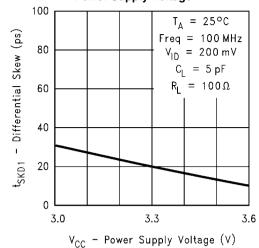
#### Differential Transition Voltage vs Power Supply Voltage



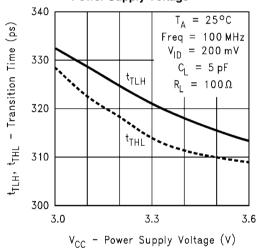
#### Differential Propagation Delay vs Ambient Temperature



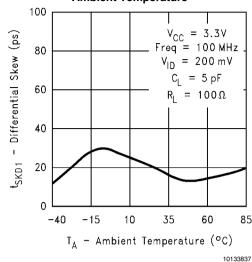
#### Differential Skew vs Power Supply Voltage



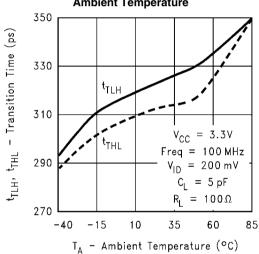
#### Transition Time vs Power Supply Voltage



#### Differential Skew vs Ambient Temperature



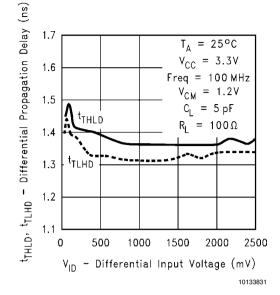
#### Transition Time vs Ambient Temperature



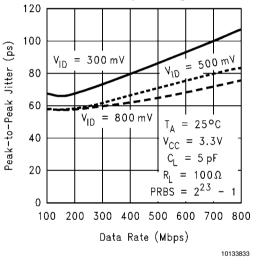
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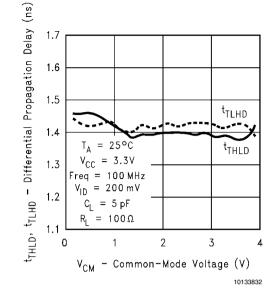
#### Differential Propagation Delay vs Differential Input Voltage



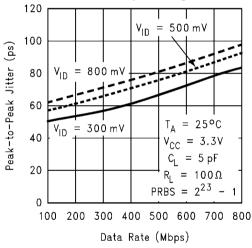
### Peak-to-Peak Output Jitter at $V_{CM} = 0.4V \text{ vs}$ Differential Input Voltage



#### Differential Propagation Delay vs Common-Mode Voltage

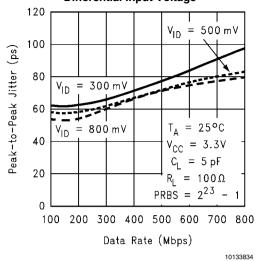


### Peak-to-Peak Output Jitter at $V_{CM} = 2.9V \text{ vs}$ Differential Input Voltage

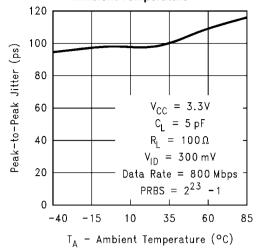


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#### Peak-to-Peak Output Jitter at V<sub>CM</sub> = 1.2V vs Differential Input Voltage

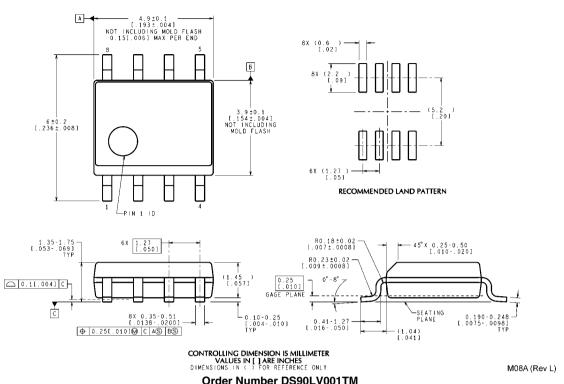


#### Peak-to-Peak Output Jitter at V<sub>CM</sub> = 1.2V vs Ambient Temperature



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## Physical Dimensions inches (millimeters) unless otherwise noted



Order Number DS90LV001TM See NS Package Number M08A

(1 (1,2) (8X 0.5)-DIMENSIONS ARE IN MILLIMETERS (8X 0.25) RECOMMENDED LAND PATTERN 1:1 RATIO WITH PKG SOLDER PADS -C 0.8 MAX (0.25) PIN 1 INDEX AREA (0.2) (0.1 TYP) (0.25) (0.15)0 3 ± 0 . 1 PIN 1 ID-∟8x 0.5±0.1 3±0.1-A 8X 0.25±0.05 Ф 0.100 C AS BS 6 X 0.5 LDA08A (Rev C) ≥ 2X 1.5 Order Number DS90LV001TLD See NS Package Number LDA08A

## **Notes**

For more National Semiconductor product information and proven design tools, visit the following Web sites at:

Pi	oducts	Design Support		
Amplifiers	www.national.com/amplifiers	WEBENCH	www.national.com/webench	
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